

M64611FP

DIGITAL SERVO MOTOR CONTROL FOR RADIO CONTROL

REJ03F0017-0100Z

Rev.1.00

Aug.26.2003

Description

The M64611FP is a semiconductor integrated circuit of the BiCMOS structure for servo motor control for the radio control application.

Features

- A quick response and a powerful holding torque
- Simple settings of dead band, pulse stretcher, boost time addition, and max duty.

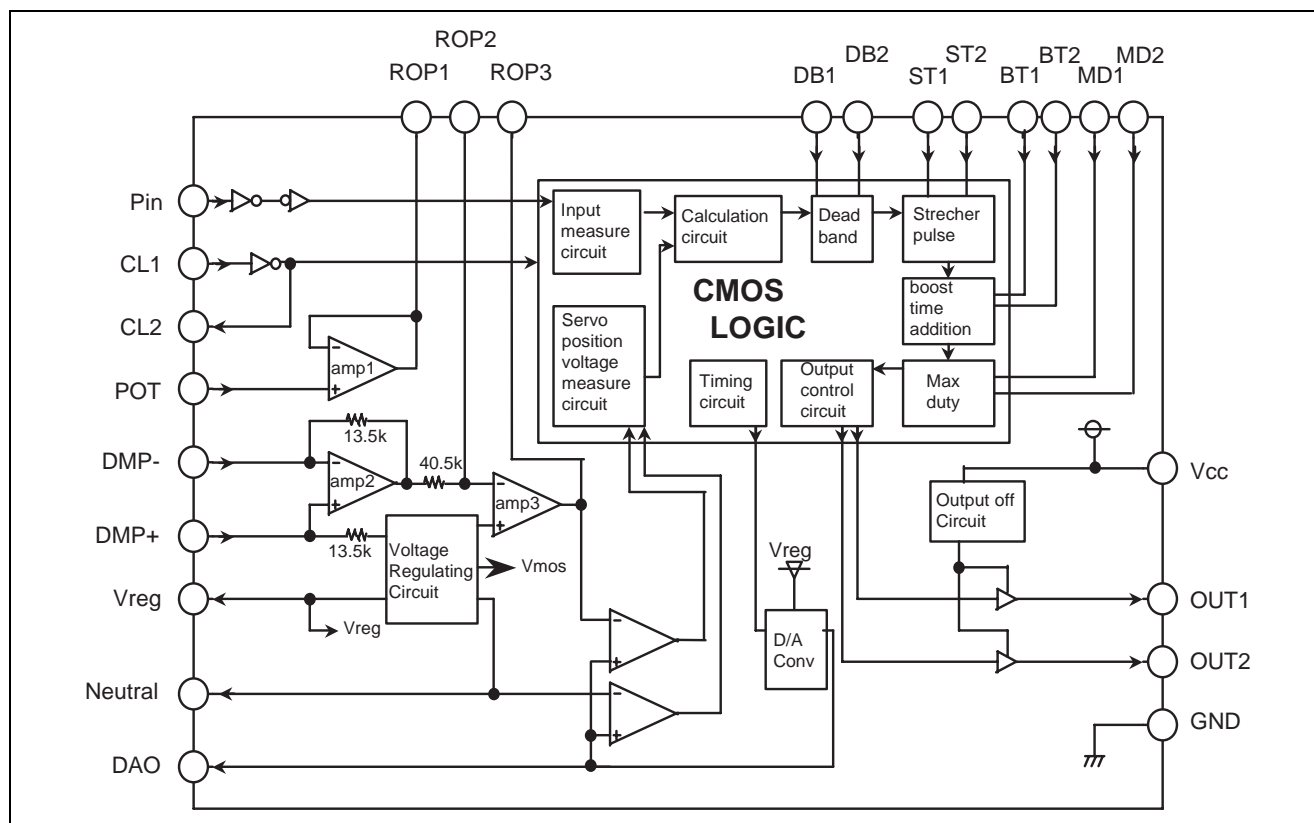
Application

- Digital proportional system for radio control

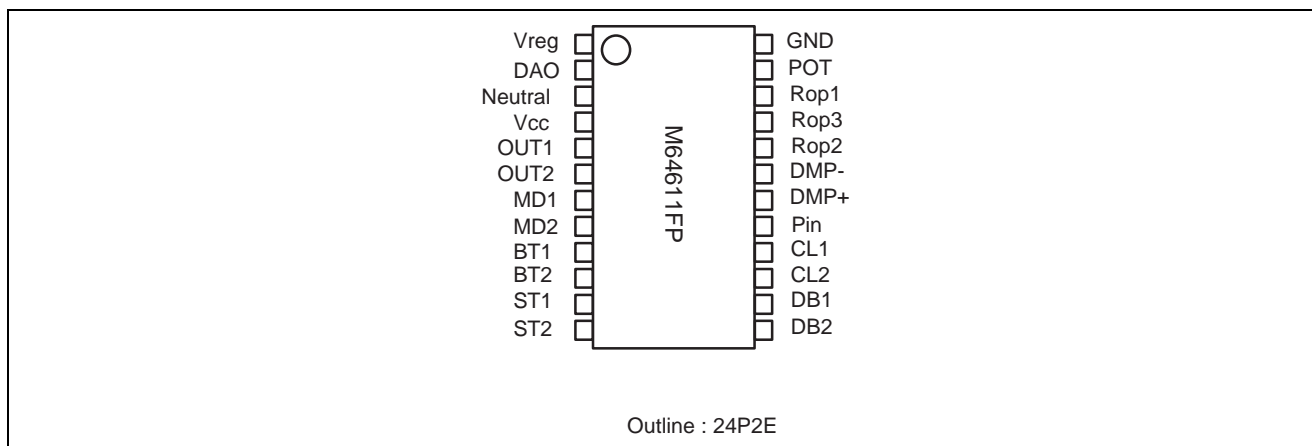
Recommended operating condition

- Supply voltage range: 4 to 9 V

Block diagram



Pin Arrangement



Pin Description

Pin No.	Symbol	Function	Notes
1	Vreg	Regulated voltage output	Connect a capacitor for the stabilization between Vreg and GND
2	DAO	D/A converter output	Connect the capacitor for the filter of 100 – 1000pF between DAO and GND.
3	Neutral	Neutral voltage output	Make it open usually. Connect a capacitor for the stabilization between Neutral and GND if Neutral voltage is unstable.
4	Vcc	Supply voltage	Connect the Electrolytic condenser more than 10 μ F and the ceramics condenser more than 0.1 μ F.
5	OUT1	Output pin 1	Connect to the external driver IC for servo drive.
6	OUT2	Output pin 2	
7	MD1	Max. duty input 1	Refer to the following input table. When it is "H" : OPEN When it is "L" : GND
8	MD2	Max. duty input 2	
9	BT1	Boost input 1	
10	BT2	Boost input 2	
11	ST1	Stretcher input 1	
12	ST2	Stretcher input 2	
13	DB2	Dead Band input 2	
14	DB1	Dead Band input 1	
15	CL2	Oscillation terminal 2	Connect to resonator between CL1 and CL2.
16	CL1	Oscillation terminal 1	
17	Pin	Receiving pulse input	Connect to the damping resistor of 100 k Ω -1 M Ω .
18	DMP+	Damping resistor input+	
19	DMP-	Damping resistor input-	
20	ROP2	Gain Adjustment Resistor 2	Connect to the resistances for adjusting Gain.
21	ROP3	Gain Adjustment Resistor 3	
22	ROP1	Gain Adjustment Resistor 1	
23	POT	Servo position voltage input	Connect the potentiometer.
24	GND	GND	

Input Table

<Dead Band >

Input		Set value
DB1	DB2	
L	L	4tosc
H	L	6tosc
L	H	9tosc
H	H	13tosc

<Max Duty >

Input		Set value
MD1	MD2	
L	L	about 97%
H	L	about 94%
L	H	about 88%
H	H	about 82%

<Boost>

Input		Set value
BT1	BT2	
L	L	12x64xtosc
H	L	28x64xtosc
L	H	64x64xtosc
H	H	116x64xtosc

<Stretcher Gain >

Input		Set value
ST1	ST2	
L	L	x 1
H	L	x 2
L	H	x 4
H	H	x 8

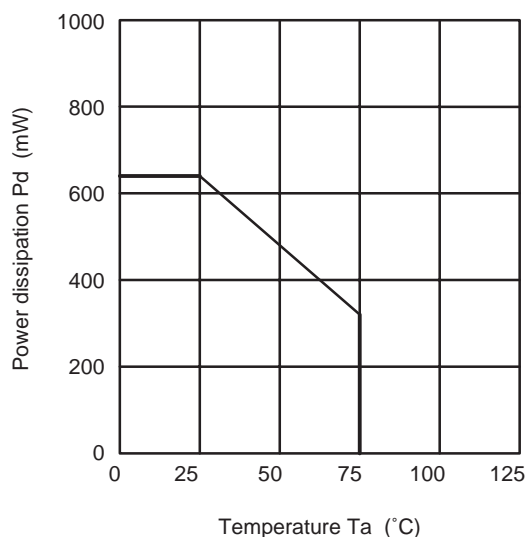
Note: tosc: oscillation period of resonator

Absolute Maximum Ratings

(Ta = -20 to 75°C, unless otherwise noted)

Symbol	Parameter	Test Conditions	Ratings	Unit
V _{CC}	Supply voltage		-0.3 to +9.0	V
I _O	Output current	OUT1, OUT2	-5 to +5	mA
P _D	Power dissipation	Ta = 25°C	630	mW
T _{opr}	Operating temperature		-20 to +75	°C
T _{stg}	Storage temperature		-40 to 125	°C

Thermal Derating (Absolute Maximum Rating)



Recommended operating conditions

(Ta = -20 to +75°C)

Symbol	Parameter	Conditions	Ratings	Unit
V _{CC}	Supply voltage		4.0 to 9.0	V
V _{INPin}	Pin input voltage		0 to V _{CC}	V
V _{INPOT}	POT input voltage		0.2 to 2.0	V
I _{OVreg}	Vreg output current		-2 to 0	mA
V _{OROP3}	ROP3 output voltage rage		0.2 to 2.0	V

Electrical Characteristics

(V_{CC} = 5V, T_a = 25°C, unless otherwise noted)

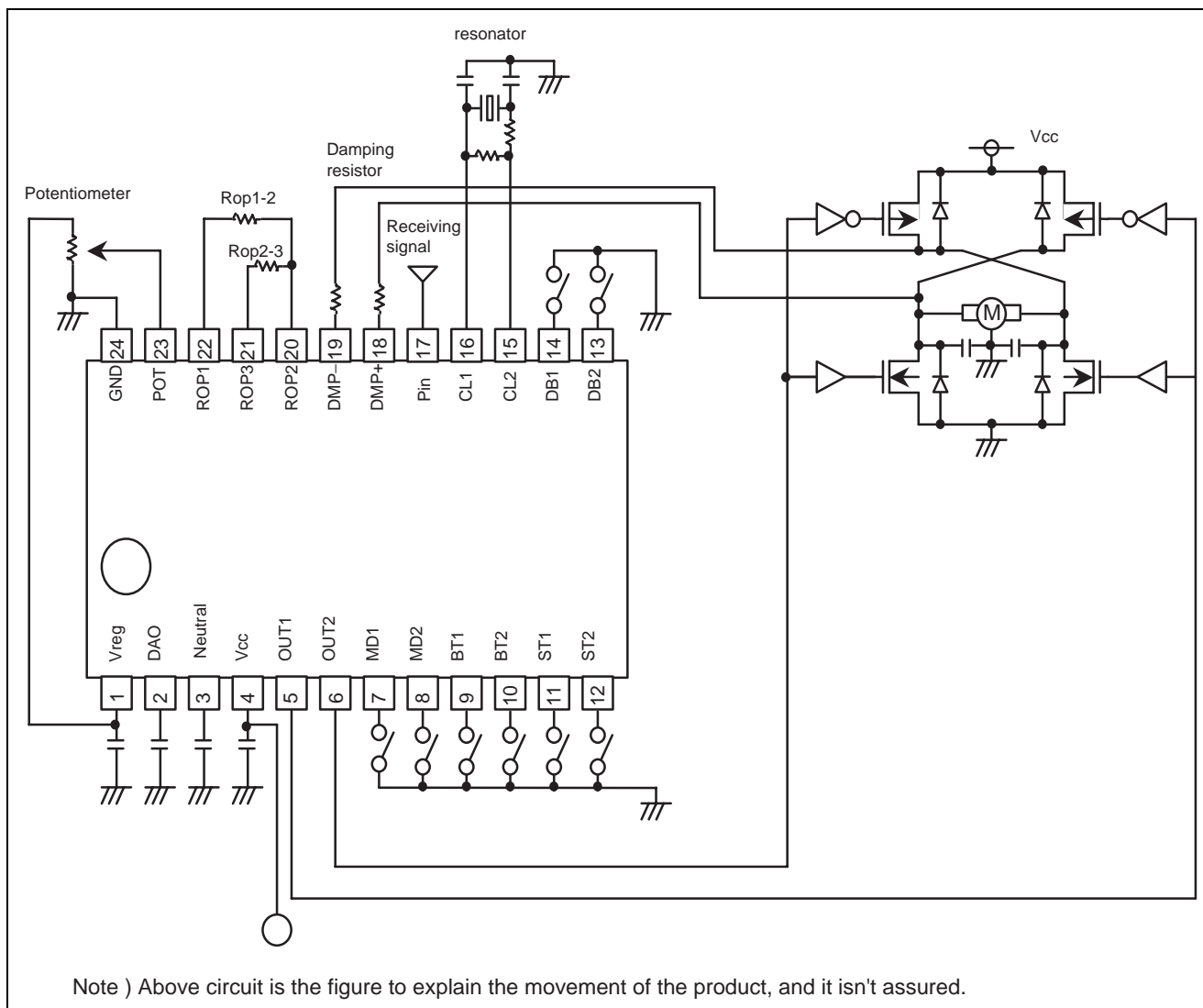
Symbol	Parameters	Test conditions	Measure Pin	Limits			Unit
				Min	Typ	Max	
I _{CC1}	Supply current 1	V _{CC1} = 9 V OUT 1 and OUT2 are OFF.	V _{CC}	—	19	28	mA
I _{CC2}	Supply current 2	V _{CC1} = 5 V OUT 1 and OUT2 are OFF.	V _{CC}	—	15	21	mA
V _{OFF}	Output voltage		V _{CC}	2.80	3.02	3.30	V
V _{ON}	Output voltage		V _{CC}	2.93	3.15	3.43	V
V _{reg1}	Regulated voltage 1	I _o = 0 μA	V _{reg}	2.02	2.15	2.28	V
V _{reg2}	Regulated voltage 2	I _o = -2 mA	V _{reg}	2.00	2.14	2.27	V
dV _{reg}	Supply Voltage dependence of V _{reg}	V _{reg1} standard. I _o = 0 μA V _{CC} = 4 to 9 (V)	V _{reg}	—	0.11	0.25	% / V
V _{Neutral}	Natural Voltage	V _{Neutral} = 0.6 V _{reg}	Natural	1.21	1.29	1.37	V
I _{OH}	“H” Output current	V _o = 0.7 V	OUT1 OUT2	-2.4	-1.54	-1.1	mA
V _{OL}	“L” Output voltage	I _o = 1 mA	OUT1 OUT2	0.02	0.1	0.3	mV
V _{OF1}	amp 1 offset voltage	POT = 1.1 V	Rop1	-10	1	10	mV
I _{IN amp1}	amp 1 input current	POT = 0.2 V	POT	-1	0.3	0	μA
V _{OH amp1}	“H” output voltage	I _o = -250 μA, POT = 2 V	Rop1	1.97	2.00	2.02	V
V _{OL amp1}	“L” output voltage	I _o = 250 μA, POT = 0.2 V	Rop1	0.18	0.20	0.23	V
G _{V1ROP3}	Voltage gain 1 (from amp2 to amp3)	Damping resistors = 300 K Ω Rop2 to 3 = 12 KΩ DMP- = 5 V, DMP+ = 0 V	Rop3	-41	-37.5	-35	dB
G _{V2ROP3}	Voltage gain 2 (from amp2 to amp3)	Damping resistors = 300 K Ω Rop2 to 3 = 12 KΩ DMP- = 5 V, DMP+ = 5 V	Rop3	-41	-37.5	-35	dB
V _{IHPin}	“H” input voltage of Pin		Pin	1.5	—	V _{CC}	V

Timing Requirement Conditions

(V_{CC} = 5 V, T_a = 25°C, unless otherwise noted)

Symbol	Parameters	Conditions	Limits			Unit
			Min	Typ.	Max	
f _{CLK}	Clock frequency		—	4.915	—	MHz
T _{wh (Pin)}	Pin “H” pulse width	f _{CLK} = 4.915 MHz	782	—	2187	μS

Application Example



Note) Above circuit is the figure to explain the movement of the product, and it isn't assured.

Notes: Be careful of handling because 1 to 4 pin and 17, 23 pin break easily to other pins.

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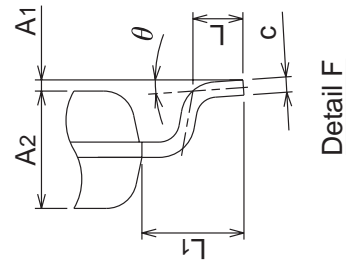
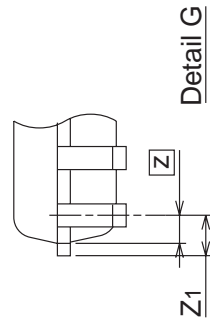
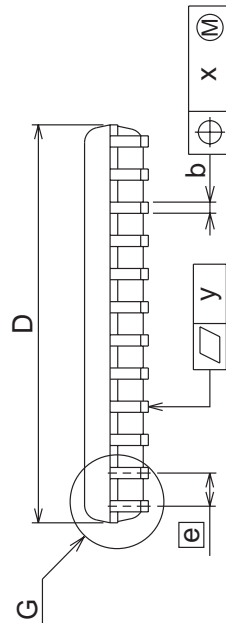
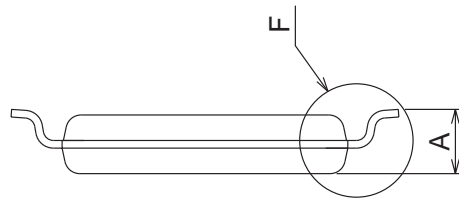
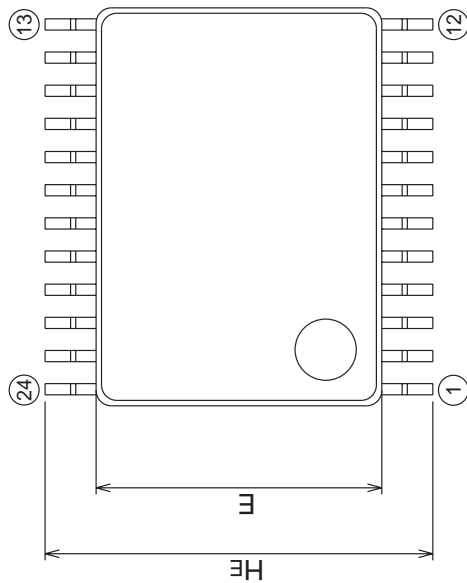
Package Dimension

24P2E-A

(MMP)

Plastic 24pin 275mil SSOP

EIAJ Package Code	JEDEC Code	Weight(g)	Lead Material
SSOP24-P-275-0.65	—	0.12	Alloy 42



Recommended Mount Pad

Symbol	Dimension in Millimeters		
	Min	Nom	Max
A	—	—	1.45
A1	0	0.1	0.2
A2	—	1.15	—
b	0.17	0.22	0.32
c	0.13	0.15	0.2
D	7.7	7.8	7.9
E	5.5	5.6	5.7
e	—	0.65	—
HE	7.4	7.6	7.8
L	0.3	0.5	0.7
L1	—	1.0	—
L2	—	0.325	—
Z1	—	—	0.475
x	—	—	0.13
y	—	—	0.1
θ	0°	—	10°
b2	—	0.35	—
e1	—	7.0	—
l2	1.0	—	—

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